Supporting Information

Modification of a polymer gate insulator by zirconium oxide doping for low temperature, high performance indium zinc oxide transistors

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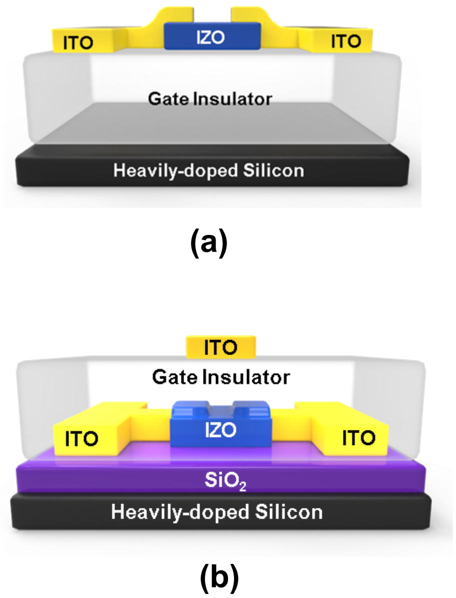

Figure S1. Schematic cross-sections of the IZO TFTs with (a) bottom gate and (b) top gate structure.